

# isc N-Channel MOSFET Transistor

# FKI06075

#### FEATURES

- Drain-source on-resistance:
  R<sub>DS</sub>(on) ≤ 8mΩ@10V
- · Fast Switching Speed
- · 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



## APPLICATIONS

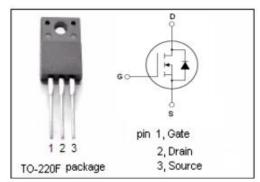
• High fast switching Power Supply

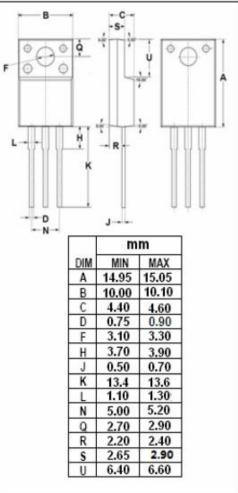
## • ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

| SYMBOL           | PARAMETER                               | VALUE   | UNIT         |  |
|------------------|---|---------|--------------|--|
| V <sub>DSS</sub> | Drain-Source Voltage                    | 60      | V            |  |
| V <sub>GS</sub>  | Gate-Source Voltage                     | ±20     | V            |  |
| ΙD               | Drain Current-Continuous                | 52      | А            |  |
| I <sub>DM</sub>  | Drain Current-Single Pulsed             | 104     | А            |  |
| $P_D$            | Total Dissipation @T <sub>C</sub> =25°C | 40      | W            |  |
| Tj               | Max. Operating Junction Temperature     | 150     | $^{\circ}$ C |  |
| T <sub>stg</sub> | Storage Temperature                     | -55~150 | $^{\circ}$   |  |

## • THERMAL CHARACTERISTICS

| SYMBOL PARAMETER    |    | MAX                                 | UNIT  |      |
|---------------------|----|-------------------------------------|-------|------|
| R <sub>th(j-c</sub> | ;) | Junction-to-case thermal resistance | 3.125 | °C/W |







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### **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25℃ unless otherwise specified

| SYMBOL              | PARAMETER                      | CONDITIONS   | MIN | ТҮР | MAX  | UNIT |
|---------------------|--------------------------------|--|-----|-----|------|------|
| BV <sub>DSS</sub>   | Drain-Source Breakdown Voltage | V <sub>GS</sub> =0V; I <sub>D</sub> = 100 μ A            | 60  |     |      | V    |
| V <sub>GS(th)</sub> | Gate Threshold Voltage         | V <sub>DS</sub> = V <sub>GS</sub> ; I <sub>D</sub> = 1mA | 1.0 |     | 2.5  | V    |
| R <sub>DS(on)</sub> | Drain-Source On-Resistance     | V <sub>GS</sub> =10V; I <sub>D</sub> =39A                |     |     | 8    | mΩ   |
| I <sub>GSS</sub>    | Gate-Source Leakage Current    | V <sub>GS</sub> = ±20V;V <sub>DS</sub> = 0V              |     |     | ±100 | nA   |
| I <sub>DSS</sub>    | Drain-Source Leakage Current   | V <sub>DS</sub> =60V; V <sub>GS</sub> = 0V               |     |     | 1    | μА   |
| V <sub>SD</sub>     | Diode forward on voltage       | I <sub>S</sub> =39A, V <sub>GS</sub> = 0 V               |     |     | 1.5  | V    |

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